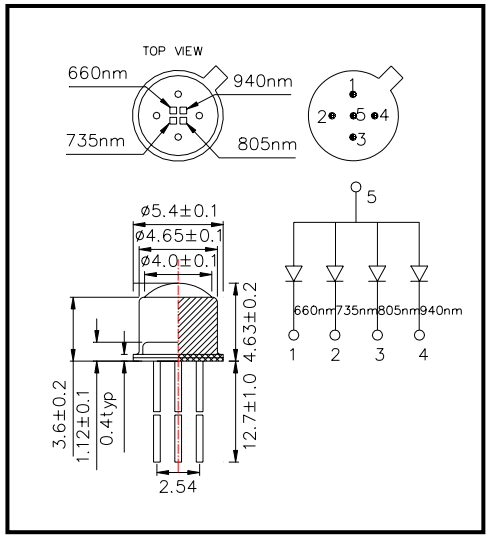
Lead (Pb) Free Product – RoHS Compliant

L660/735/805/940-40B42 multi-wavelength LED

L660/735/805/940-40B42 consists of an AlGaAs (660, 735, 805nm) and GaAs(940nm) LEDs mounted on TO-18 5pins type stem with an un-spherical glass lens. Chips are connected as anode common.

♦Outer dimension (Unit: mm)



♦Specifications

1) Product Name	Multi-wavelength LED Lamp
2) Type No.	L735/805/850-40B32
3) Chip	
(1) Chip material	AlGaAs
(2) Peak wavelength	735, 805, 850nm
4) Package	
(1) Stem	TO-18 5pin type
(2) Lens	Φ5 spherical glass

♦Absolute Maximum Ratings [Ta=25°C]

Item	Symbol	Maximum Rated Value				Unit
		660	735	805	940	
Power Dissipation	PD	120	180	170	140	mW
Forward Current	IF	50	75	100	100	mA
Pulse Forward Current	IF	200	200	300	1000	mA
Reverse Voltage	VR	5				V
Operating Temperature	TOPR	-20 ~ +80				°C
Storage Temperature	TSTG	-30 ~ +100				°C
Soldering Temperature	TSOL	240				°C

‡Soldering condition: Soldering condition must be completed within 3 seconds at 240°C and is allowed in the area apart 3mm from the bottom of the lamp.

♦Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Wavelength	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	660	IF=20mA		1.9	2.2	V
		735					
		805			1.5	1.7	
		940			1.2	1.3	
Reverse Current	IR		VR=5V			10	u A
Total Output Power	PO	660	IF=20mA		2.9		mW
		735			3.5		
		805			3.5		
		940			2.5		
Radiant Intensity	Ie	660	IF=20mA				mW/sr
		735					
		805					
		940					
Peak Wavelength	λP	660	IF=20mA	650	655	660	nm
		735		725	735	745	
		805		795	805	820	
		940		935	940	955	
Half Wavelength	Δλ	660	IF=20mA		20		nm
		735			30		
		805			35		
		940			45		

‡Total Radiated Power is measured by Photodyne #500

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